

AMENDMENTS TO THE SPECIFICATION:

Please amend page 6, line 11, through page 7, line 4, of the Specification as follows:

A method for manufacturing a thin film transistor comprising the steps of forming a first region and a second region; discharging a composition containing a mask formation material to a region across the second region and the first region; flowing a part of the composition containing the mask formation material discharged to the first region into the second region to form a mask; removing a part of the first region by using the mask to form a fourth region and to form a third region by removing the mask; discharging a composition containing a conductive material to a region across the fourth region and the third region; flowing a composition containing the conductive material in the third region into the fourth region to form a first electrode layer and a second electrode layer; and flowing a part of the composition discharged to the first region into the second region; wherein wettability with respect to the composition containing the mask formation material of the first region is lower than that of the second composition, and wettability with respect to the conductive material of the third region is lower than that of the fourth region.